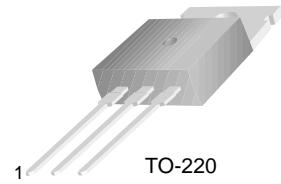


KSC2333

High Speed Switching Application

- Low Collector Saturation Voltage
- Specified of Reverse Biased SOA With Inductive Load



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	2	A
I_{CP}	*Collector Current (Pulse)	4	A
I_B	Base Current (DC)	1	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	15	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

*PW≤350μs, Duty Cycle≤10%

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$V_{CEO(\text{sus})}$	Collector-Emitter Sustaining Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}, L = 1\text{mH}$	400		V
$V_{CEX(\text{sus})1}$	Collector-Emitter Sustaining Voltage	$I_C = 0.5\text{A}, I_{B1} = -I_{B2} = 0.1\text{A}$ $T_C = 125^\circ\text{C}, L = 180\mu\text{H}$, clamped	450		V
$V_{CEX(\text{sus})2}$	Collector-Emitter Sustaining Voltage	$I_C = 1\text{A}, I_{B1} = 0.2\text{A}, -I_{B2} = 0.2\text{A}$ $T_C = 125^\circ\text{C}, L = 180\mu\text{H}$, clamped	400		V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 400\text{V}, I_E = 0$		10	μA
I_{CER}	Collector Cut-off Current	$V_{CE} = 400\text{V}, R_{BE} = 51\Omega, T_C = 125^\circ\text{C}$		1	mA
I_{CEX1}	Collector Cut-off Current	$V_{CE} = 400\text{V}, V_{BE(\text{off})} = -5\text{V}$		10	μA
I_{CEX2}	Collector Cut-off Current	$V_{CE} = 400\text{V}, V_{BE(\text{off})} = -5\text{V} @$ $T_C = 125^\circ\text{C}$		1	mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$		10	μA
h_{FE1} h_{FE2}	* DC Current Gain	$V_{CE} = 5\text{V}, I_C = 0.1\text{A}$ $V_{CE} = 5\text{V}, I_C = 0.5\text{A}$	20 10	80	
$V_{CE(\text{sat})}$	* Collector-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$		1	V
$V_{BE(\text{sat})}$	* Base-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$		1.2	V
t_{ON}	Turn ON Time	$V_{CC} = 150\text{V}, I_C = 0.5\text{A}$		1	μs
t_{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.1\text{A}$		2.5	μs
t_F	Fall Time	$R_L = 300\Omega$		1	μs

* Pulse Test: PW≤350μs, Duty Cycle≤2%Pulsed

h_{FE} Classification

Classification	R	O	Y
h_{FE1}	20 ~ 40	30 ~ 60	40 ~ 80

Typical Characteristics

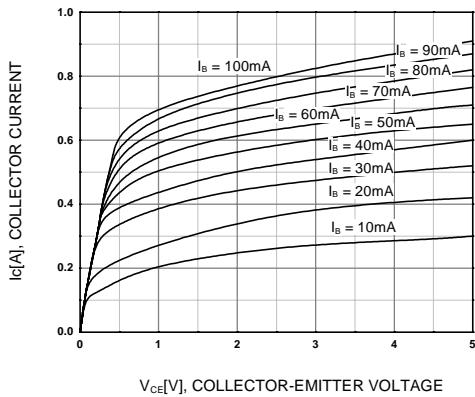


Figure 1. Static Characteristic

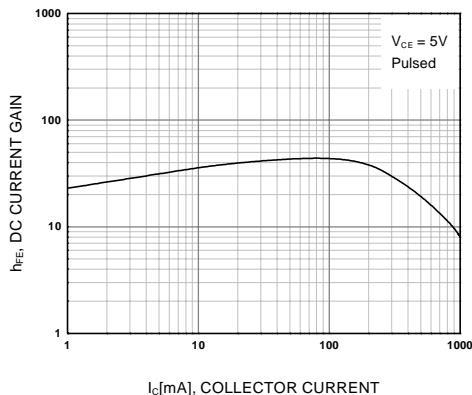
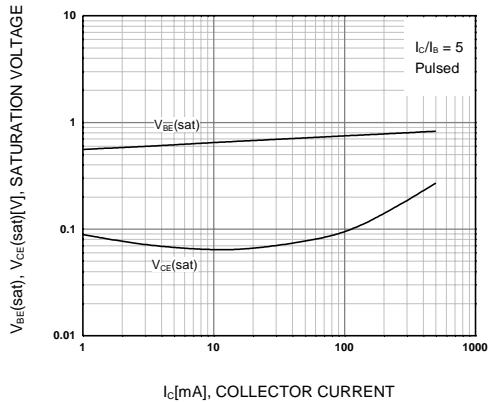
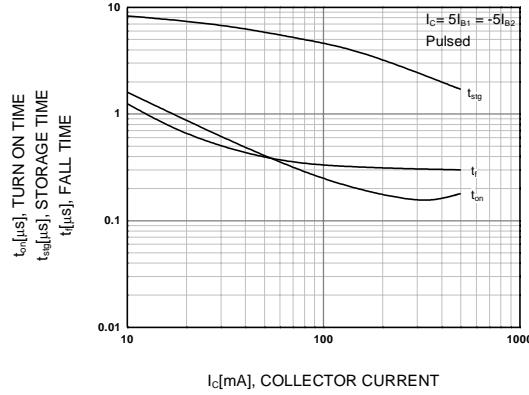


Figure 2. DC current Gain



**Figure 3. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage**



**Figure 4. Turn On, Storage and Fall Time
vs Collector Current**

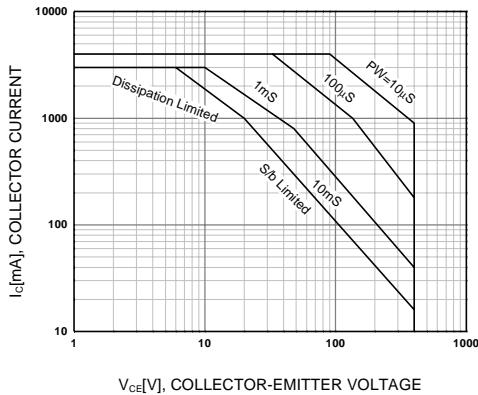


Figure 5. Forward Bias Safe Operating Area

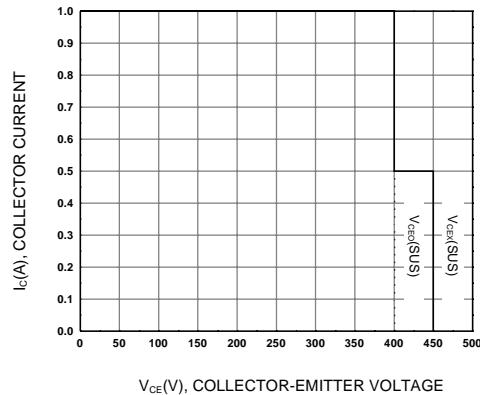


Figure 6. Reverse Bias Safe Operating Area